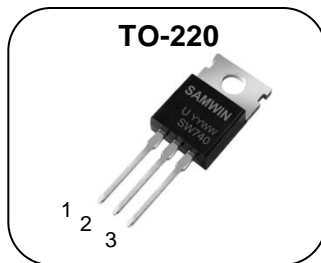


N-channel TO-220 MOSFET

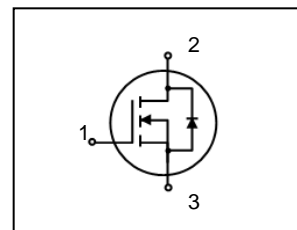
Features

- High ruggedness
- $R_{DS(ON)}$ (Max 0.55Ω)@ $V_{GS}=10V$
- Gate Charge (Typical 38nC)
- Improved dv/dt Capability
- 100% Avalanche Tested



1. Gate 2. Drain 3. Source

BV_{DSS}	: 400V
I_D	: 10A
$R_{DS(ON)}$: 0.55ohm



General Description

This power MOSFET is produced with advanced VDMOS technology of SAMWIN. This technology enable power MOSFET to have better characteristics, such as fast switching time, low on resistance, low gate charge and especially excellent avalanche characteristics. It is mainly suitable for half bridge or full bridge resonant topology like a electronic ballast, and also low power switching mode power appliances.

Order Codes

Item	Sales Type	Marking	Package	Packaging
1	SW P 740U	SW740	TO-220	TUBE

Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DSS}	Drain to Source Voltage	400	V
I_D	Continuous Drain Current (@ $T_C=25^{\circ}C$)	10*	A
	Continuous Drain Current (@ $T_C=100^{\circ}C$)	6.3*	A
I_{DM}	Drain current pulsed (note 1)	40	A
V_{GS}	Gate to Source Voltage	± 30	V
E_{AS}	Single pulsed Avalanche Energy (note 2)	1200	mJ
E_{AR}	Repetitive Avalanche Energy (note 1)	170	mJ
dv/dt	Peak diode Recovery dv/dt (note 3)	5	V/ns
P_D	Total power dissipation (@ $T_C=25^{\circ}C$)	226	W
	Derating Factor above 25°C	1.8	W/°C
T_{STG}, T_J	Operating Junction Temperature & Storage Temperature	-55 ~ + 150	°C
T_L	Maximum Lead Temperature for soldering purpose, 1/8 from Case for 5 seconds.	300	°C

Thermal characteristics

Symbol	Parameter	Value	Unit
R_{thjc}	Thermal resistance, Junction to case	0.55	°C/W
R_{thcs}	Thermal resistance, Case to Sink	0.5	°C/W
R_{thja}	Thermal resistance, Junction to ambient	58	°C/W

Electrical characteristic ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
Off characteristics						
BV_{DSS}	Drain to source breakdown voltage	$V_{GS}=0V, I_D=250\mu A$	400			V
$\Delta BV_{DSS} / \Delta T_J$	Breakdown voltage temperature coefficient	$I_D=250\mu A$, referenced to 25°C		0.43		V/ $^\circ\text{C}$
I_{DSS}	Drain to source leakage current	$V_{DS}=400V, V_{GS}=0V$			1	μA
		$V_{DS}=320V, T_C=125^\circ\text{C}$			50	μA
I_{GSS}	Gate to source leakage current, forward	$V_{GS}=30V, V_{DS}=0V$			100	nA
	Gate to source leakage current, reverse	$V_{GS}=-30V, V_{DS}=0V$			-100	nA
On characteristics						
$V_{GS(TH)}$	Gate threshold voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	2.0		4.0	V
$R_{DS(ON)}$	Drain to source on state resistance	$V_{GS}=10V, I_D = 5A$		0.35	0.55	Ω
G_{fs}	Forward Transconductance	$V_{DS}=20V, I_D = 5 A$	10			S
Dynamic characteristics						
C_{iss}	Input capacitance	$V_{GS}=0V, V_{DS}=25V, f=1\text{MHz}$		1150		pF
C_{oss}	Output capacitance			170		
C_{rss}	Reverse transfer capacitance			40		
$t_{d(on)}$	Turn on delay time	$V_{DS}=200V, I_D=10A, R_G=25\Omega$ (note 4,5)		15	30	ns
t_r	Rising time			35	60	
$t_{d(off)}$	Turn off delay time			98	200	
t_f	Fall time			38	80	
Q_g	Total gate charge	$V_{DS}=320V, V_{GS}=10V, I_D=10A$ (note 4,5)		38	70	nC
Q_{gs}	Gate-source charge			6		
Q_{gd}	Gate-drain charge			18		

Source to drain diode ratings characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_S	Continuous source current	Integral reverse p-n Junction diode in the MOSFET			10	A
I_{SM}	Pulsed source current				40	A
V_{SD}	Diode forward voltage drop.	$I_S=10A, V_{GS}=0V$			1.5	V
T_{rr}	Reverse recovery time	$I_S=10A, V_{GS}=0V,$ $di_f/dt=100A/\mu s$		270		ns
Q_{rr}	Reverse recovery Charge				2.53	μC

※. Notes

1. Repetitive rating : pulse width limited by junction temperature.
2. $L = 25.4\text{mH}, I_{AS} = 10A, V_{DD} = 50V, R_G=25\Omega$, Starting $T_J = 25^\circ\text{C}$
3. $I_{SD} \leq 10A, di/dt = 100A/\mu s, V_{DD} \leq BV_{DSS}$, Starting $T_J = 25^\circ\text{C}$
4. Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$
5. Essentially independent of operating temperature.

Fig. 1. On-state characteristics

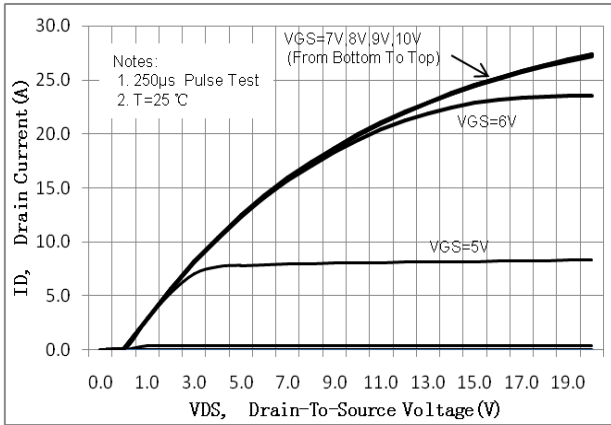


Fig. 2. On-resistance variation vs. drain current and gate voltage

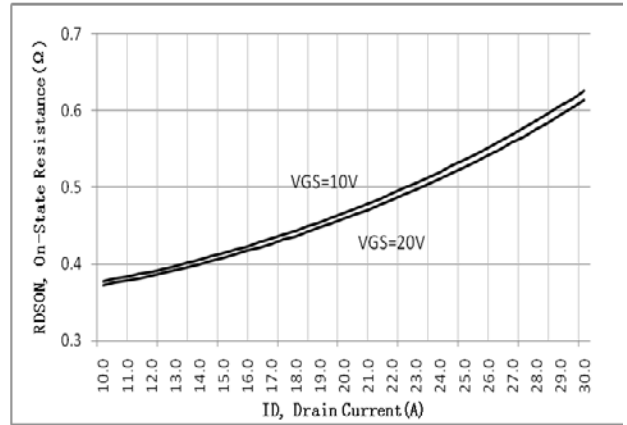


Fig. 3. Gate charge characteristics

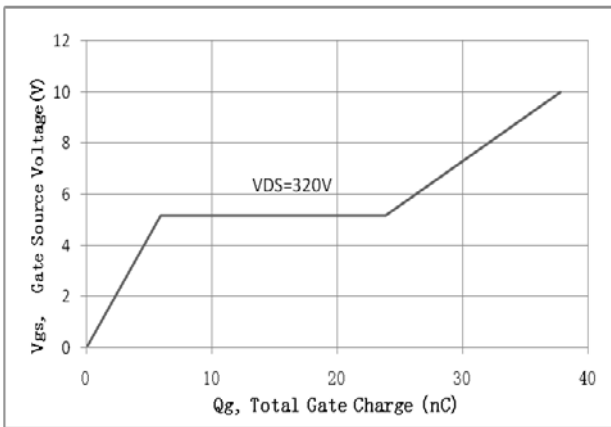


Fig. 4. On state current vs. diode forward voltage

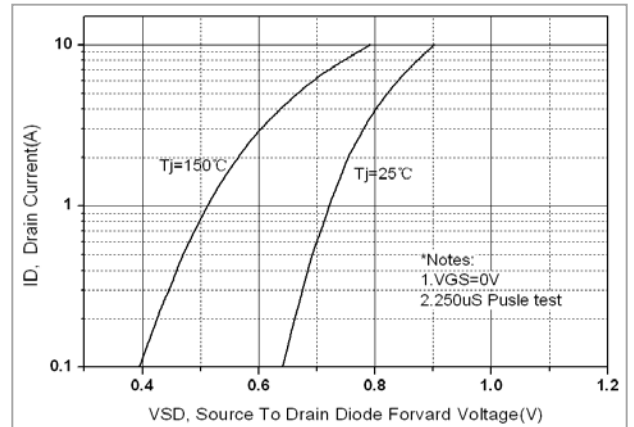


Fig 5. Breakdown Voltage Variation vs. Junction Temperature

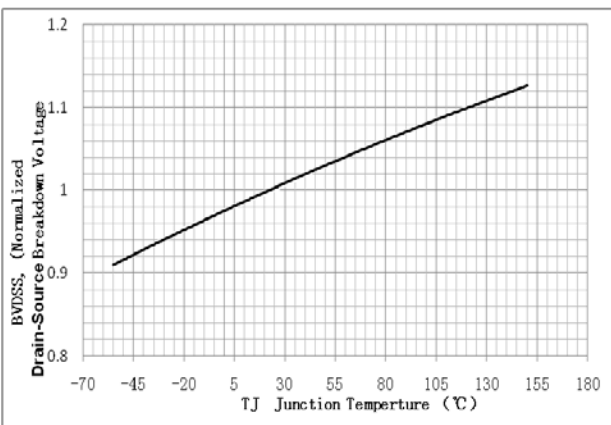


Fig. 6. On resistance variation vs. junction temperature

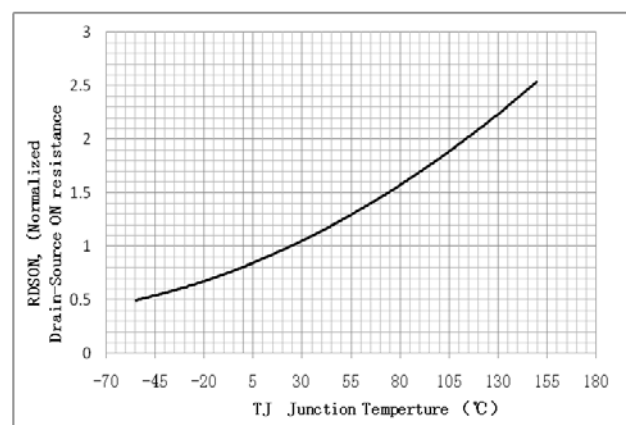


Fig. 7. Maximum safe operating area

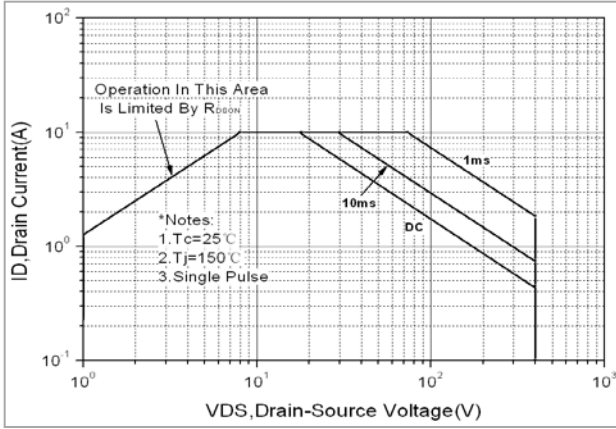


Fig. 8. Transient thermal response curve

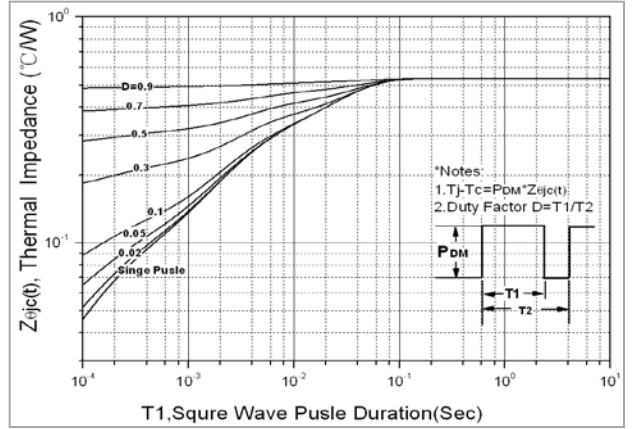


Fig. 9. Gate charge test circuit & waveform

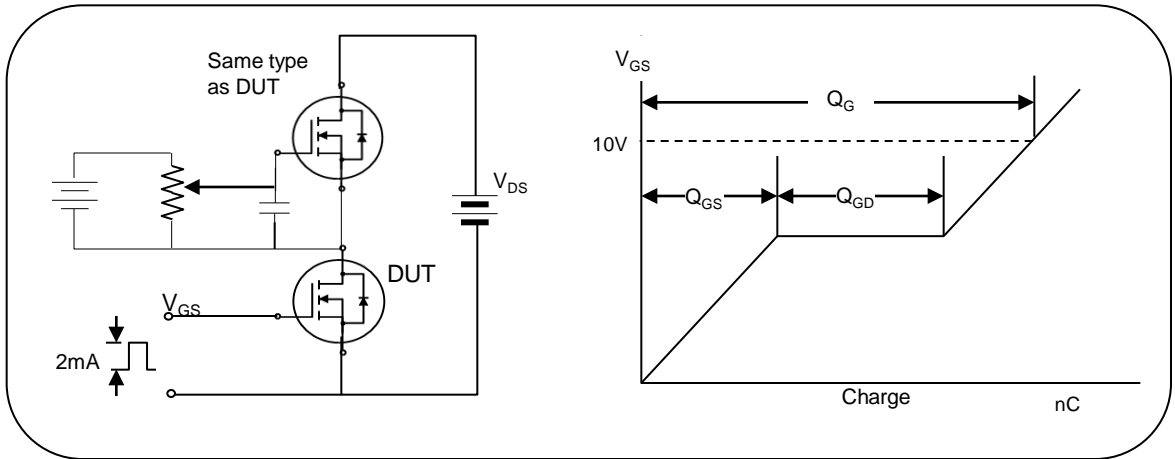


Fig. 10. Switching time test circuit & waveform

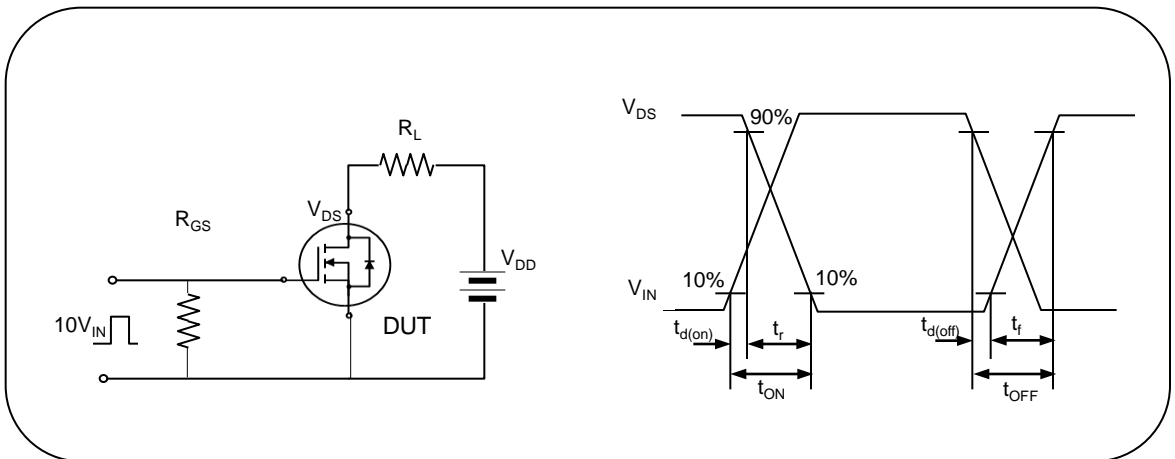


Fig. 11. Unclamped Inductive switching test circuit & waveform

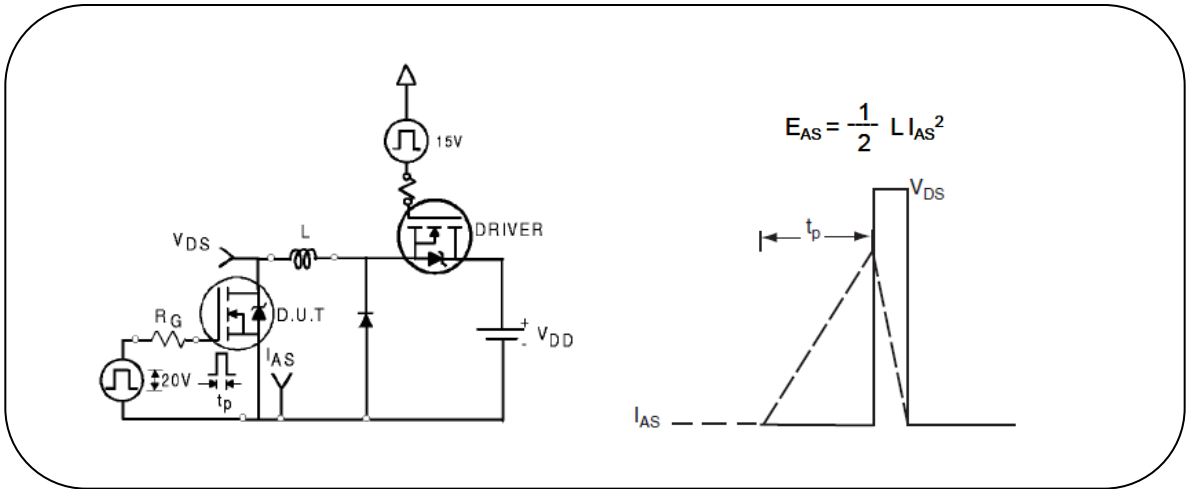


Fig. 12. Peak diode recovery dv/dt test circuit & waveform

